

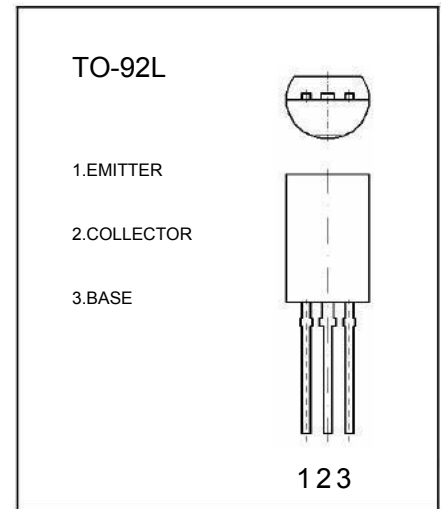


# TO-92L Plastic-Encapsulate Transistors

## C2632 TRANSISTOR (NPN)

### FEATURES

Low collector to emitter saturation voltage  $V_{CE(sat)}$ .  
Complementary pair with A1124



### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Units
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current –Continuous	0.05	A
$P_C$	Collector Power Dissipation	1.0	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}, I_B=0$	150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=100\text{V}, I_E=0$			1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	130		330	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=30\text{mA}, I_B=3\text{mA}$			1	V
Transition frequency	$f_T$	$V_{CB}=10\text{V}, I_C=10\text{mA}$ $f=1\text{MHz}$		160		MHz

### CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S
Range	130-220	185-330